International TOR Rectifier

HFA30PA60C

HEXFRED™

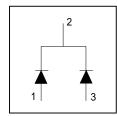
Ultrafast, Soft Recovery Diode

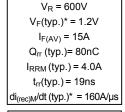
Features

- · Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- Specified at Operating Conditions
 Benefits

Delielles

- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- · Higher Frequency Operation
- Reduced Snubbing
- · Reduced Parts Count







Description

International Rectifier's HFA30PA60C is a state of the art center tap ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 volts and 15 amps per Leg continuous current, the HFA30PA60C is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the to portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA30PA60C is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

Absolute Maximum Ratings (per Leg)

Absolute maximum reatings (per Leg)							
Parameter		Max.	Units				
V _R	Cathode-to-Anode Voltage	600	V				
I _F @ T _C = 100°C	Continuous Forward Current	15					
I _{FSM}	Single Pulse Forward Current	150	Α				
I _{FRM}	Maximum Repetitive Forward Current	60					
P _D @ T _C = 25°C	Maximum Power Dissipation	74	w				
P _D @ T _C = 100°C	Maximum Power Dissipation	29					
TJ	Operating Junction and	FE to 11F0	С				
T _{STG}	Storage Temperature Range	-55 to +150					

^{* 125°}C

Electrical Characteristics (per Leg) @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions		
V _{BR}	Cathode Anode Breakdown Voltage	600	_		V	I _R = 100μA		
V _{FM}	Max Forward Voltage	T	1.3	1.7	V	I _F = 15A		
			1.5	2.0		I _F = 30A	See Fig. 1	
			1.2	1.6		I _F = 15A, T _J = 125°C	3	
I _{RM}	Max Reverse Leakage Current		1.0	10	μA	V _R = V _R Rated	See Fig. 2	
			400	1000		$T_J = 125^{\circ}C, V_R = 0.8 \text{ x } V_R \text{ Rated}$		
Ст	Junction Capacitance	Τ	25	50	pF	V _R = 200V	See Fig. 3	
L _S	Series Inductance		12	2	nН	Measured lead to lead	5mm from	
	Series inductance				ш	package body		

Dynamic Recovery Characteristics (per Leg)@ T_J = 25°C (unless otherwise specified)

_			-			•	
	Parameter	Min.	Тур.	Max.	Units	Test Conditions	
t _{rr}	Reverse Recovery Time		19	_		$I_F = 1.0A$, $di_f/dt = 200A/\mu s$, $V_R = 30V$	
t _{rr1}	See Fig. 5, 10		42	60	ns	T _J = 25°C	
t _{rr2}			70	120		T _J = 125°C	I _F = 15A
I _{RRM1}	Peak Recovery Current		4.0	6.0	Α	T _J = 25°C	
I _{RRM2}	See Fig. 6		6.5	10	^	T _J = 125°C	V _R = 200V
Q _{rr1}	Reverse Recovery Charge		80	180	nC	T _J = 25°C	
Q _{rr2}	See Fig. 7		220	600		T _J = 125°C	$di_f/dt = 200A/\mu s$
di _{(rec)M} /dt1	Peak Rate of Fall of Recovery Current	_	250		A/µs	T _J = 25°C	
di _{(rec)M} /dt2	During t _b See Fig. 8		160		γνμs	T _J = 125°C	

Thermal - Mechanical Characteristics (per Leg)

	Parameter	Min.	Тур.	Max.	Units	
T _{lead} ①	Lead Temperature			300	°C	
R _{thJC}	Junction-to-Case, Single Leg Conducting			1.7	K/W	
	Junction-to-Case, Both Legs Conducting			0.85		
R _{thJA} @	Thermal Resistance, Junction to Ambient			40		
R _{thCS} ③	Thermal Resistance, Case to Heat Sink		0.25			
Wt	Weight		6.0		g	
			0.21		(oz)	
	Mounting Torque	6.0		12	Kg-cm	
	mountaing rollquo	5.0		10	lbf•in	

① 0.063 in. from Case (1.6mm) for 10 sec

Typical Socket Mount
 Mounting Surface, Flat, Smooth and Greased

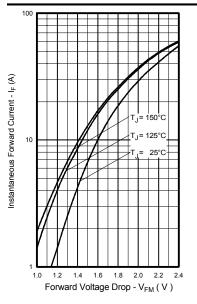


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current, (per Leg)

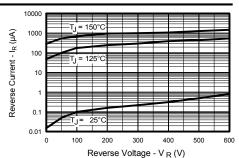


Fig. 2 - Typical Reverse Current vs. Reverse Voltage, (per Leg)

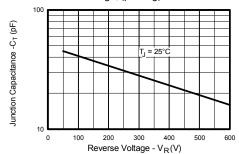


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage, (per Leg)

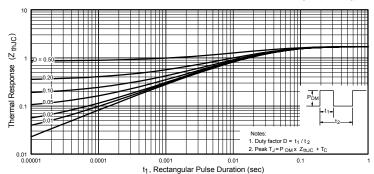


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics, (per Leg)

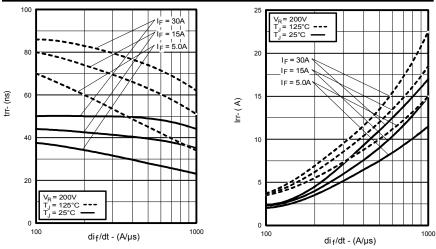
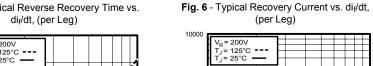


Fig. 5 - Typical Reverse Recovery Time vs. di_f/dt, (per Leg)



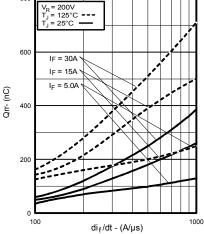


Fig. 7 - Typical Stored Charge vs. dif/dt, (per Leg)

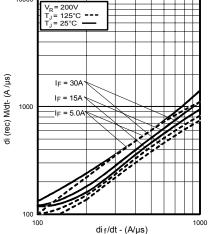


Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_f/dt , (per Leg)

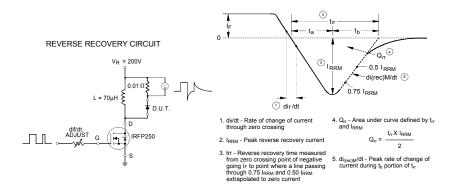
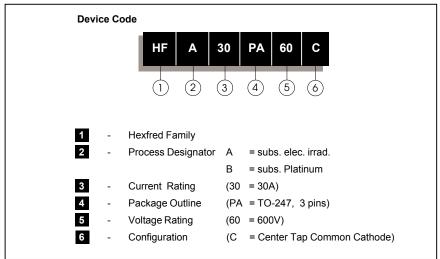


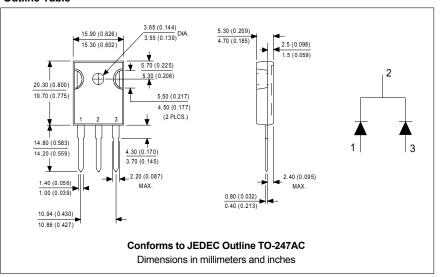
Fig. 9 - Reverse Recovery Parameter Test Circuit

Fig. 10 - Reverse Recovery Waveform and Definitions

Ordering Information Table



Outline Table



Data and specifications subject to change without notice.

This product has been designed and qualified for Industrial Level.

Qualification Standards can be found on IR's Web site.

International

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Visit us at www.irf.com for sales contact information. 05/01